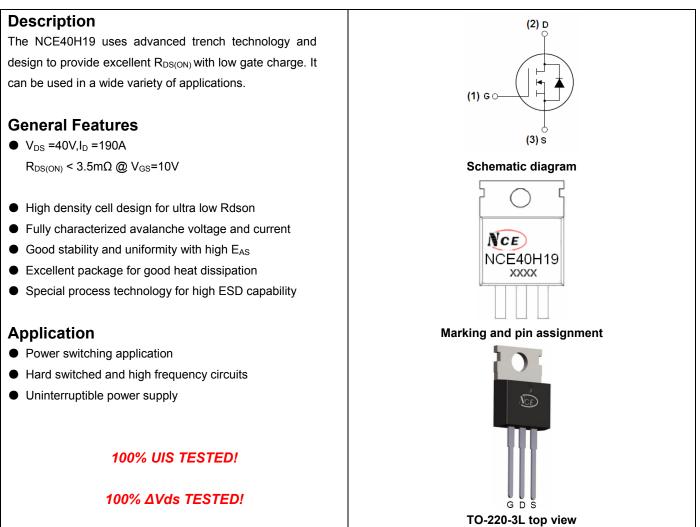


NCE40H19

NCE N-Channel Enhancement Mode Power MOSFET



Package Marking and Ordering Information

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity
NCE40H19	NCE40H19	TO-220-3L	-	-	-

Absolute Maximum Ratings (T_A=25℃unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	Vds	40	V
Gate-Source Voltage	Vgs	±20	V
Drain Current-Continuous	Ι _D	190	A
Drain Current-Continuous(T _C =100 ℃)	I _D (100℃)	134	А
Pulsed Drain Current	I _{DM}	750	А
Maximum Power Dissipation	PD	220	W
Derating factor		1.47	W/℃
Single pulse avalanche energy (Note 5)	E _{AS}	1400	mJ
Operating Junction and Storage Temperature Range	TJ,TSTG	-55 To 175	°C





Thermal Characteristic

|--|

Electrical Characteristics (T_A=25°C unless otherwise noted)

Parameter	Symbol	Condition	Min	Тур	Max	Unit
Off Characteristics	·					
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V I _D =250µA	40		-	V
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =40V,V _{GS} =0V	-	-	1	μA
Gate-Body Leakage Current	I _{GSS}	V _{GS} =±20V,V _{DS} =0V	-	-	±100	nA
On Characteristics (Note 3)						
Gate Threshold Voltage	V _{GS(th)}	V _{DS} =V _{GS} ,I _D =250µA	2	3	4	V
Drain-Source On-State Resistance	R _{DS(ON)}	V _{GS} =10V, I _D =40A	-	2.4	3.5	mΩ
Forward Transconductance	g fs	V _{DS} =50V,I _D =75A	170	-	-	S
Dynamic Characteristics (Note4)						
Input Capacitance	C _{lss}		-	6500	-	PF
Output Capacitance	C _{oss}	V _{DS} =25V,V _{GS} =0V, F=1.0MHz	-	916	-	PF
Reverse Transfer Capacitance	C _{rss}		-	780	-	PF
Switching Characteristics (Note 4)						
Turn-on Delay Time	t _{d(on)}		-	26	-	nS
Turn-on Rise Time	tr	V_{DD} =30V,I _D =2A,R _L =15 Ω	-	24	-	nS
Turn-Off Delay Time	t _{d(off)}	V _{GS} =10V,R _G =2.5Ω	-	91	-	nS
Turn-Off Fall Time	t _f		-	39	-	nS
Total Gate Charge	Qg	\/ − 20\/ − 20 ∧	-	163		nC
Gate-Source Charge	Q _{gs}	V _{DS} =30V,I _D =30A, V _{GS} =10V	-	31		nC
Gate-Drain Charge	Q _{gd}	V _{GS} =10V	-	64		nC
Drain-Source Diode Characteristics	·					
Diode Forward Voltage (Note 3)	V _{SD}	V _{GS} =0V,I _S =40A	-		1.2	V
Diode Forward Current (Note 2)	I _S		-	-	190	А
Reverse Recovery Time	t _{rr}	TJ = 25°C, IF = 40A	-	42	60	nS
Reverse Recovery Charge	Qrr	di/dt = 100A/µs(Note3)	-	66	80	nC
Forward Turn-On Time	t _{on}	Intrinsic turn-on time is negligible (turn-on is dominated by LS+LD)				

Notes:

- 1. Repetitive Rating: Pulse width limited by maximum junction temperature.
- **2.** Surface Mounted on FR4 Board, $t \le 10$ sec.
- **3.** Pulse Test: Pulse Width \leq 300µs, Duty Cycle \leq 2%.
- 4. Guaranteed by design, not subject to production
- 5. EAS condition: Tj=25 $^\circ \!\! \mathbb{C}, V_{DD} \!\! = \!\! 20V, V_G \!\! = \!\! 10V, L \!\! = \!\! 0.5mH, Rg \!\! = \!\! 25\Omega$



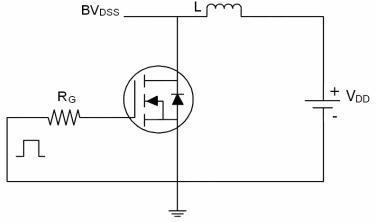
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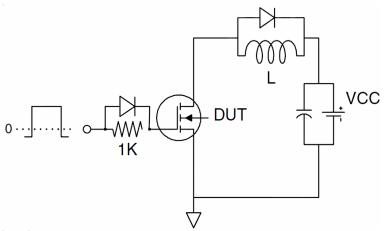


Test circuit

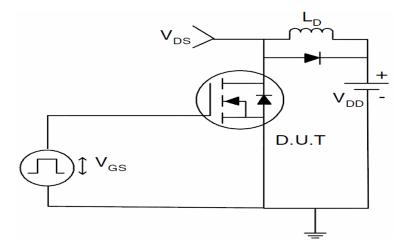
1) E_{AS} test Circuits



2) Gate charge test Circuit:



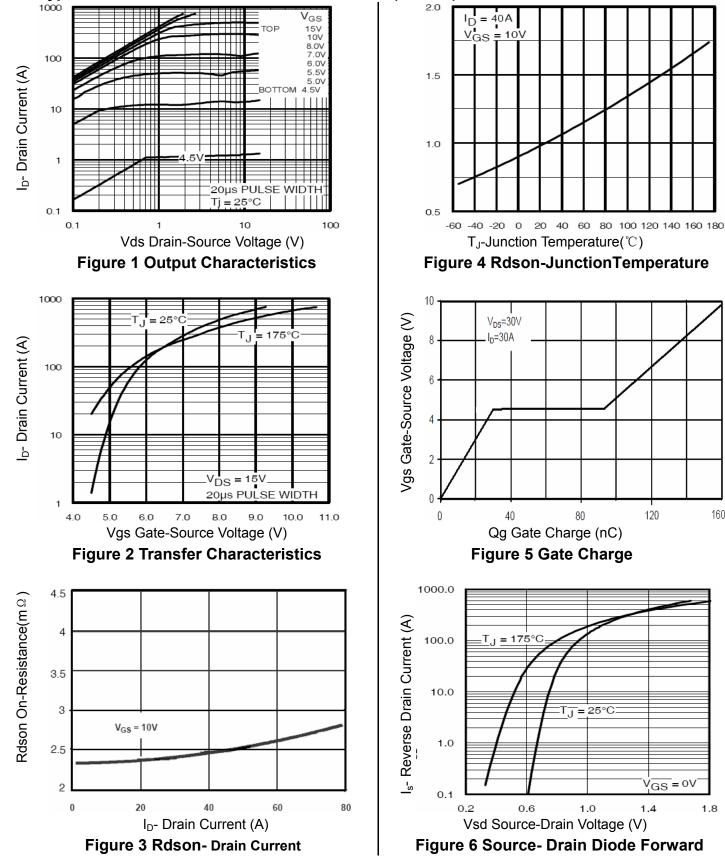
3) Switch Time Test Circuit







Typical Electrical and Thermal Characteristics (Curves)



1.8

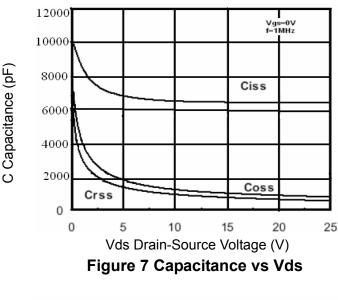
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Pb Free Product

NCE40H19



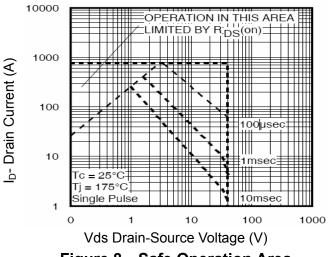


Figure 8 Safe Operation Area

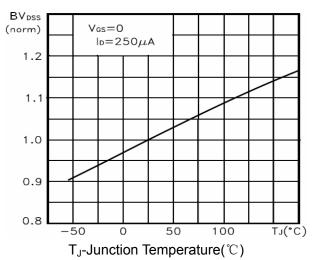


Figure 9 BV_{DSS} vs Junction Temperature

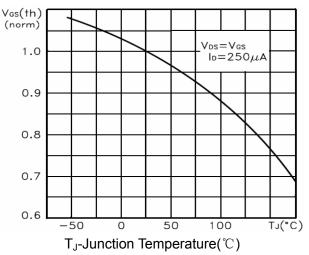
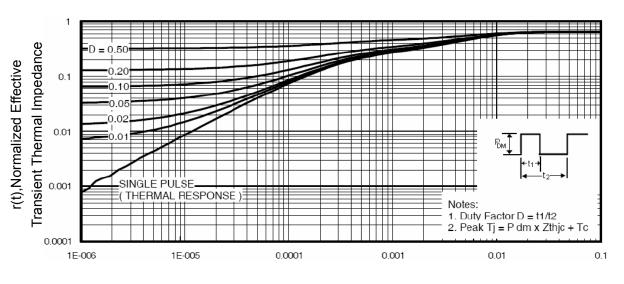
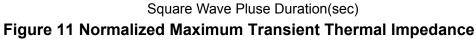


Figure 10 V_{GS(th)} vs Junction Temperature





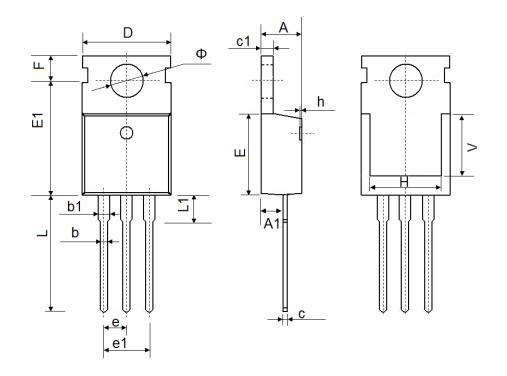


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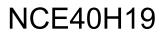
TO-220-3L Package Information



Symbol	Dimensions	In Millimeters	Dimensions In Inches		
	Min.	Max.	Min.	Max.	
А	4.400	4.600	0.173	0.181	
A1	2.250	2.550	0.089	0.100	
b	0.710	0.910	0.028	0.036	
b1	1.170	1.370	0.046	0.054	
С	0.330	0.650	0.013	0.026	
c1	1.200	1.400	0.047	0.055	
D	9.910	10.250	0.390	0.404	
E	8.9500	9.750	0.352	0.384	
E1	12.650	12.950	0.498	0.510	
е	2.540 TYP.		0.100 TYP.		
e1	4.980	5.180	0.196	0.204	
F	2.650	2.950	0.104	0.116	
Н	7.900	8.100	0.311	0.319	
h	0.000	0.300	0.000	0.012	
L	12.900	13.400	0.508	0.528	
L1	2.850	3.250	0.112	0.128	
V	7.500 REF.		0.295 REF.		
Ф	3.400	3.800	0.134	0.150	







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